Abstracts

A simple bias dependant LF FET noise model for CAD

I. Angelov, R. Kozhuharov and H. Zirath. "A simple bias dependant LF FET noise model for CAD." 2001 MTT-S International Microwave Symposium Digest 01.1 (2001 Vol. I [MWSYM]): 407-410 vol.1.

Extensive multi-bias low frequency noise (LFN) measurements were performed on MESFET, HEMT and InP HEMT devices in order to obtain a simple bias dependent LF noise model usable in CAD tools and consistent with small and large signal models and high frequency noise models. The model was experimentally evaluated with a 10 GHz DRO and good correspondence was obtained between the modelled and measured LFN.

❑ Return to main document.

Click on title for a complete paper.